

### **Abstract**

The present invention relates to a polishing pad for use in a chemical mechanical planarization (CMP) process of semiconductors, to a process for preparing the same, and to a process for preparing a semiconductor device using the same. The polishing pad according to an embodiment can achieve low hardness by comprising a polishing layer formed using a curing agent of specific components. It is possible to enhance the mechanical properties of the polishing pad, as well as to improve the surface defects appearing on the surface of a semiconductor substrate, by controlling the surface roughness reduction rate and the recovery elasticity index of the polishing pad to specific ranges. It is also possible to further enhance the polishing rate.

[Representative drawing]

Fig. 5